Abstract

Method for the treatment of a semiconductor wafer

The invention relates to a method for the treatment of a semiconductor wafer 5, in which the semiconductor wafer 5

- is treated in a liquid container 11 filled at least partly with a solution 91 containing hydrogen fluoride, such that oxide situated on the surface of the semiconductor wafer 5 dissolves,
- is transported out of the solution 91 along a transport direction 81 and dried, and
- is treated with an ozone-containing gas 93 after drying, such that the surface of the semiconductor wafer 5 is oxidized,

wherein one part of the surface of the semiconductor wafer 5 already comes into contact with the ozone-containing gas 93 while another part of the surface of the semiconductor wafer 5 is still in contact with the solution 91, and wherein the solution 91 and the ozone-containing gas 93 are spatially separated in such a way that they do not come into contact with one another.

Fig. 1